

Power Matters.™

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Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.75	V
DC Current Gain	HFE	70.00		200.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			100.00	V
Collector Current (dc)	I _C			5.00	A
Collector-Emitter Voltage (Base Open)	V _{CEO}			80.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			5.50	V
Power Dissipation, Total	P _T			25.00	W

This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor
- ▶ Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor

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